# Driving AI Efficiency through Heterogeneously Integrated Data-Centric Computing

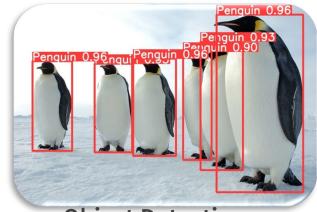
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**Bourns College of Engineering** 



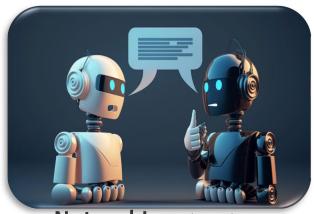
# Wide-Ranging Applications of Al







**Autonomous Navigation** 



Natural Language



**Malware Detection** 



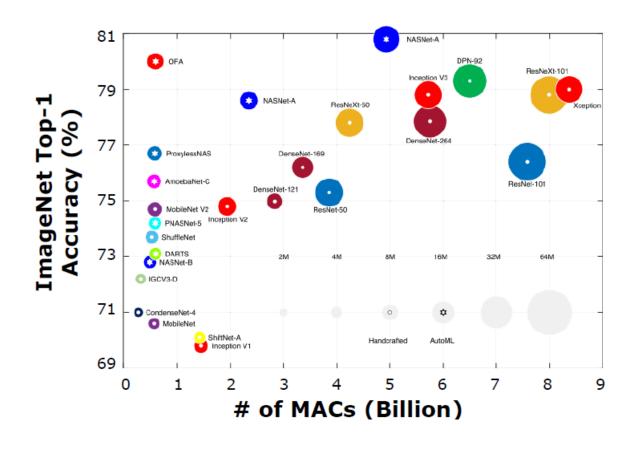
**Medical Diagnosis** 

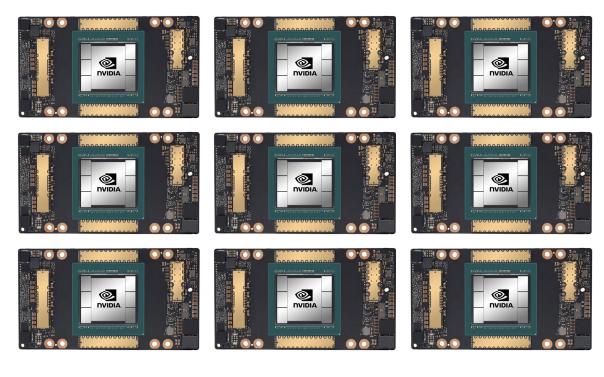


**Drug Discovery** 



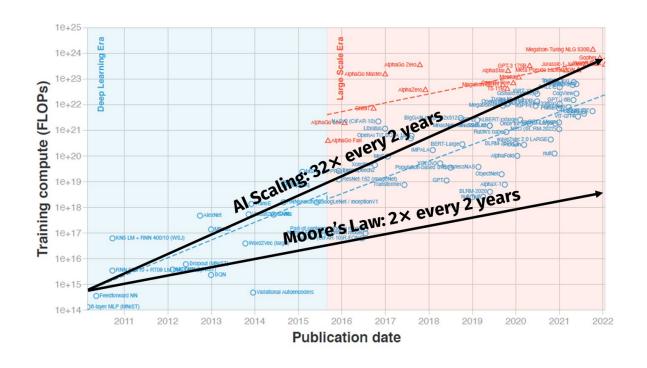
# **Recent Triumphs of Deep Learning**

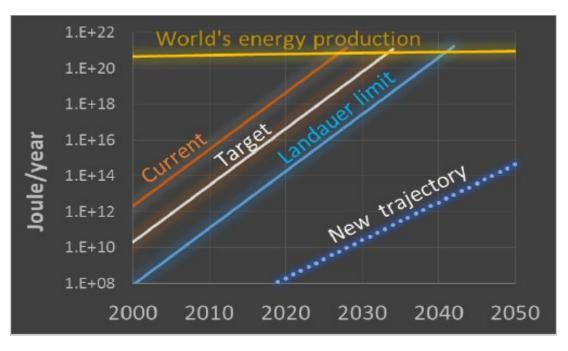






### Grand Challenge: Computational Efficiency

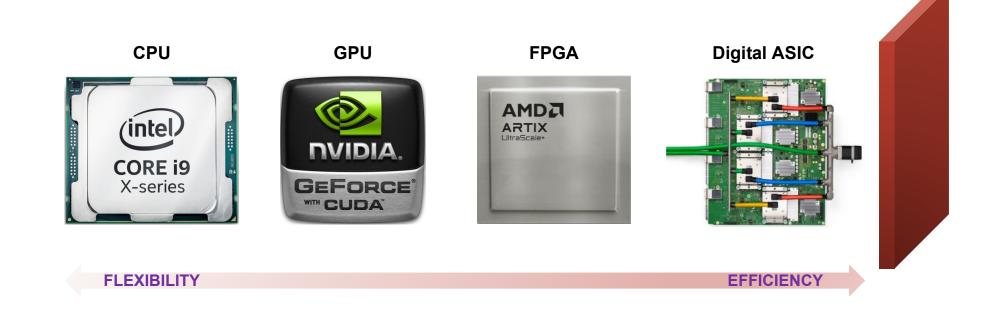






### Landscape of Today's Computing Systems

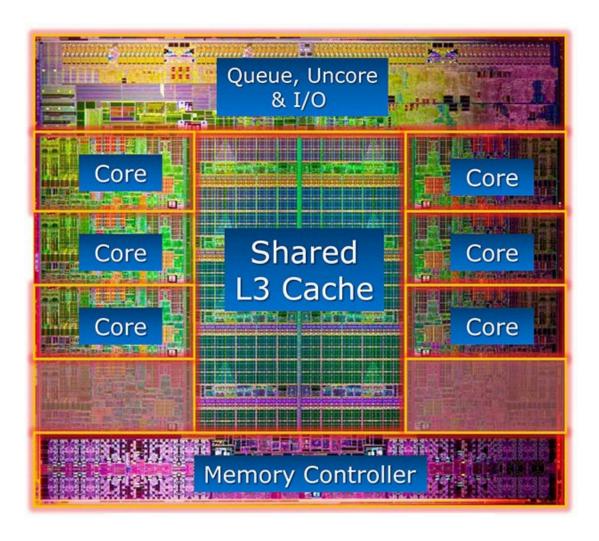
Memory Wall



They are all processor-centric platforms

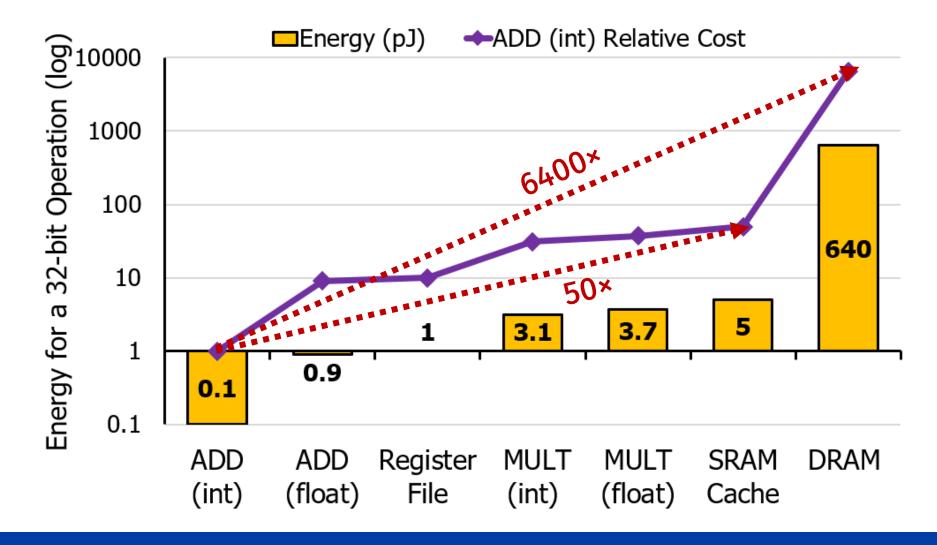


### **Processor-Centric Systems**



- Imbalanced computing systems
  - Most of the system is dedicated to storing and moving data
  - Processing is done only in processors
- Yet, system energy and latency are still bottlenecked by data

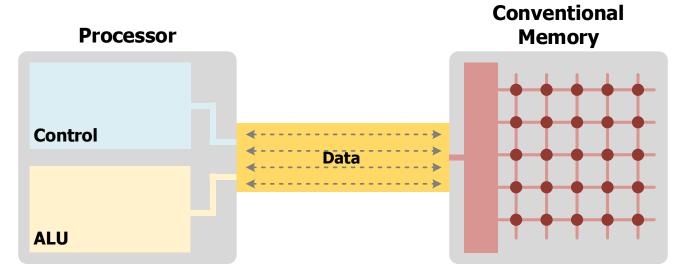
#### **Cost of Data Movement**





### **Paradigm Shift of Computing**

• Challenge: Processing is performed far away from where data is stored



- Paradigm shift towards data-centric computing to:
  - ✓ enable computation close to or in memory
  - ✓ shorten distance of data movement
  - ✓ reduce dimensionality of data



### **Outline**

- Theme 1: Emerging Computing Paradigms
- Enable computation inside memory
- Theme 2: More-than-Moore Heterogenous System
- Shorten distance of data movement
- Theme 3: Algorithm/Hardware Co-Design
- Reduce volume of data movement

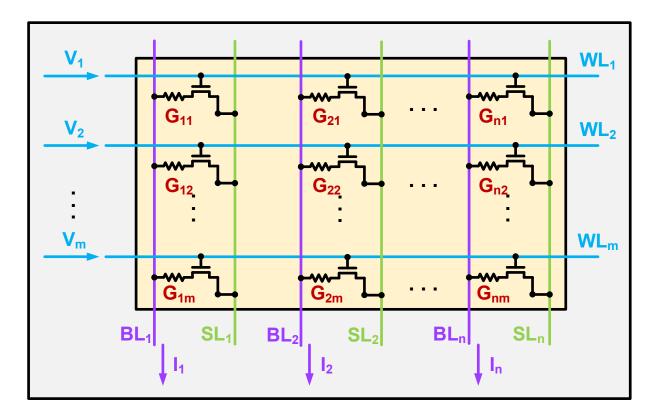


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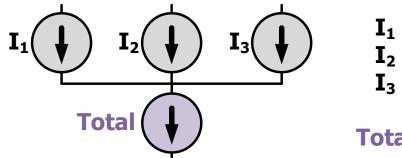
### Compute-in-Memory as MAC Accelerator



Multiply: logical AND

V (input)	G (conductance)	Out (bitline)
0	0	0
0	1	0
1	0	0
1	1	1

• Accumulate: current summation



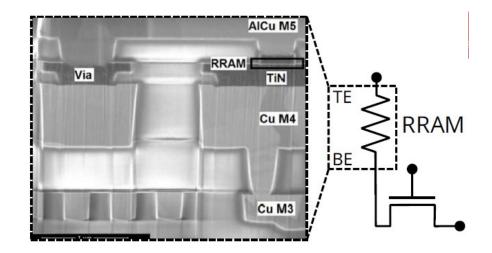
$$I_1 = 1 \mu A$$
  
 $I_2 = 3 \mu A$   
 $I_3 = 2 \mu A$ 

Total =  $6 \mu A$ 

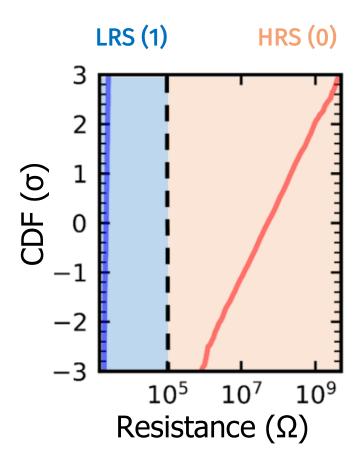
### RRAM-based CIM for Al

- Benefits of resistive RAM (RRAM) for CIM
  - Non-volatile on-chip storage of model parameters
    High capacity with possible multi-level cell

  - Low leakage during standby

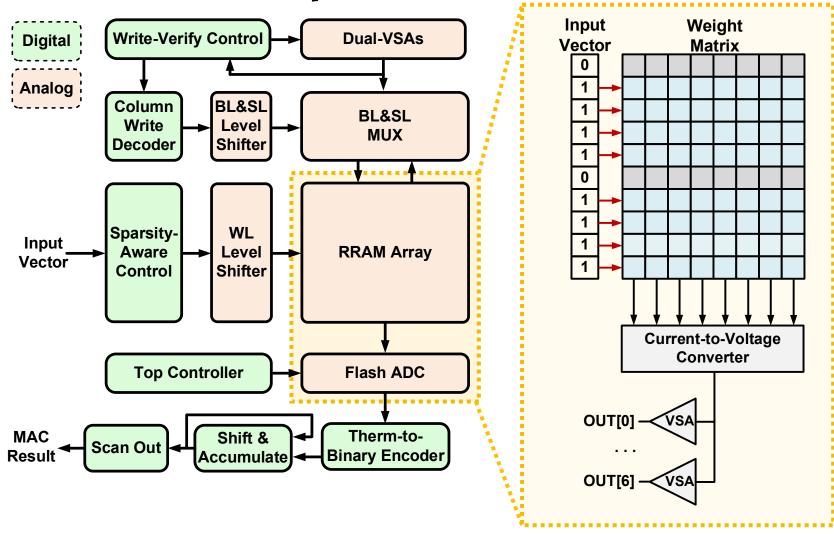


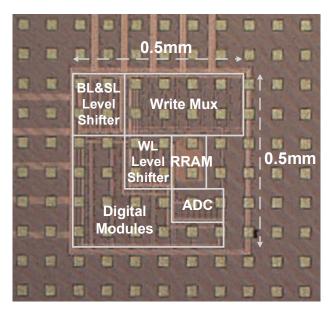
• Low-power and low-cost AI inference in embedded electronics





### **RRAM-CIM Tape-out**

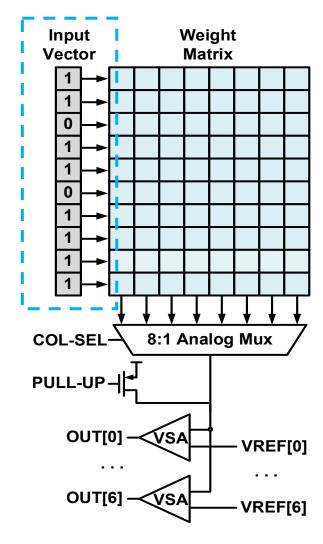




Test chip taped-out in TSMC 40-nm node with embedded 1T1R RRAM



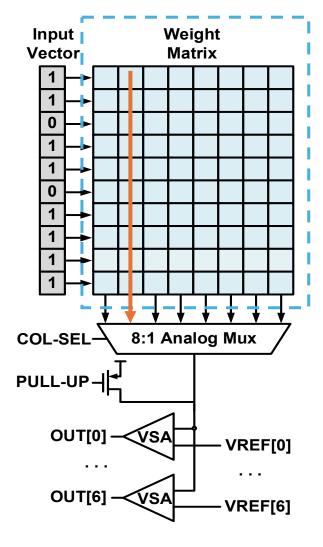
### **Compute Scheme: Input Activations**



- Opening multiple wordlines (WLs) at once enable parallelized MAC operations
- Each input bit asserts one WL
- Input controller ensures 7 activated WLs for each set of computation



### **Compute Scheme: Weight Storage**

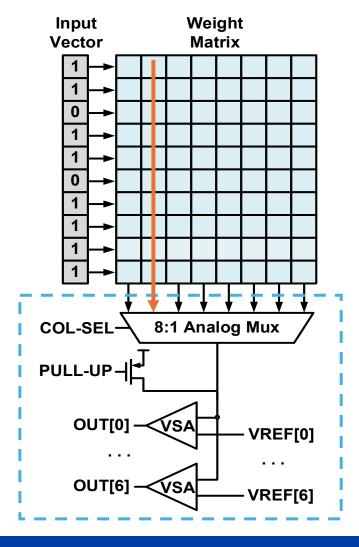


- Weights are stored in 1T1R cells
  - HRS denotes '0' and LRS denotes '1'
  - Reconfigurable weight precision

	W1[3]	W1[2]	W1[1]	W1[0]	W0[3]	W0[2]	W0[1]	W0[0]
4-bit weight								
	W3[1]	W3[0]	W2[1]	W2[0]	W1[1]	W1[0]	W0[1]	W0[0]
2-bit weight								
	W7[0]	W6[0]	W5[0]	W4[0]	W3[0]	W2[0]	W1[0]	W0[0]
1-bit weight								



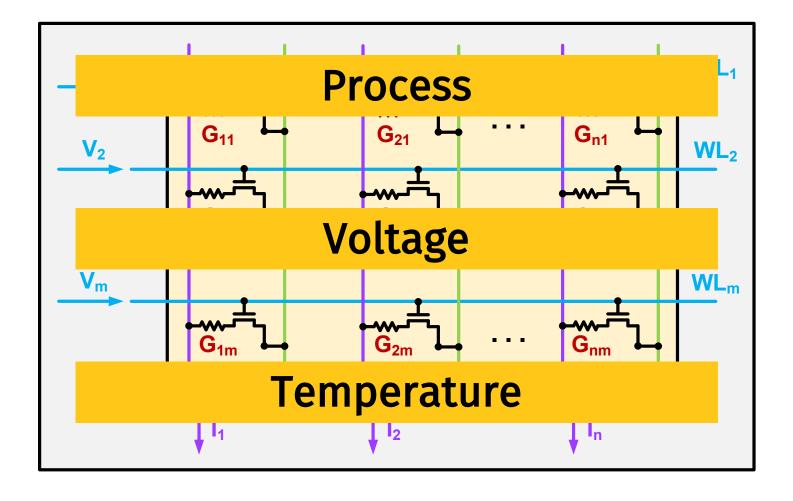
# Compute Scheme: Peripheral Sensing



- 8:1 mux for time-multiplexing
- Resistive divider between RRAM cells and pull-up PMOS
- BL voltage sensed by 3-bit flash ADC (7 voltage sense amplifiers)
- 7-bit ADC thermometer output is encoded as 3-bit binary

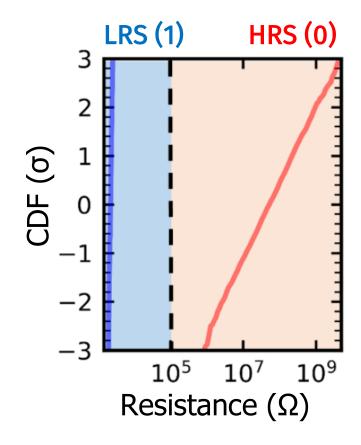


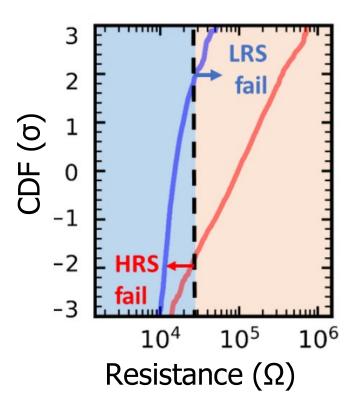
### Design Challenges in RRAM-based CIM





# **Challenge: Device Process Variation**

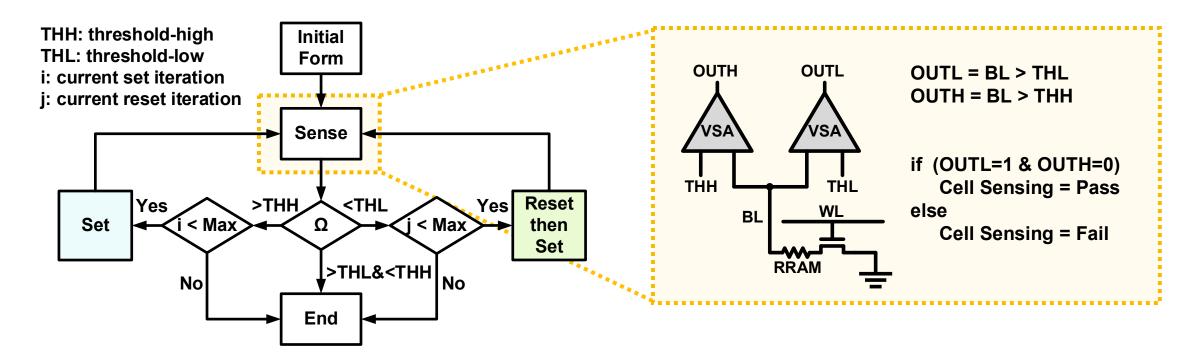






### **On-Chip Write-Verify for CIM**

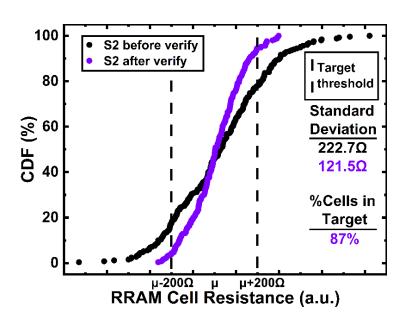
- High-speed on-chip programming of RRAM cells for CIM applications
  - Two thresholds (THH & THL) make up a resistance window

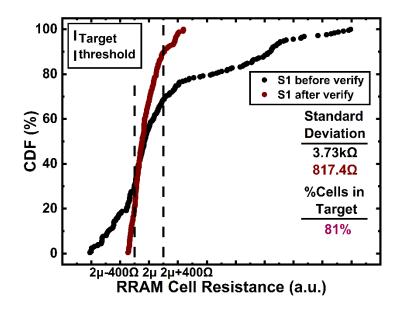


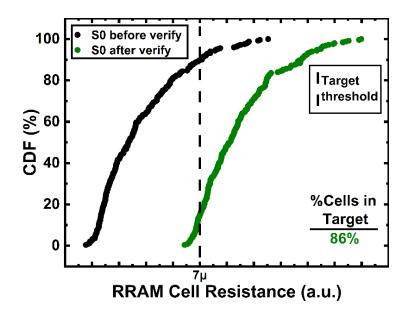


### **Write-Verify Measurement Results**

- >80% cells can be in programmed in target with on-chip write-verify
- Achieve 10<sup>5</sup> programming speedup compared to off-chip programming equipment

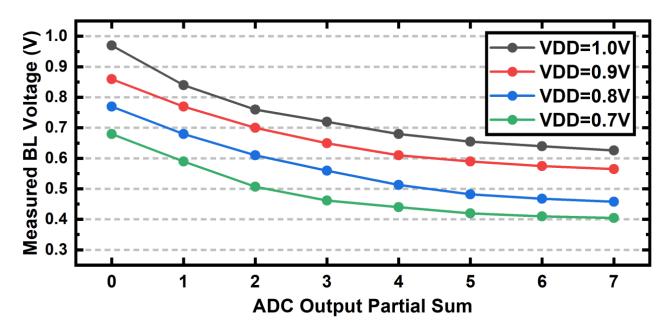






### Challenge: Supply Voltage Toggling

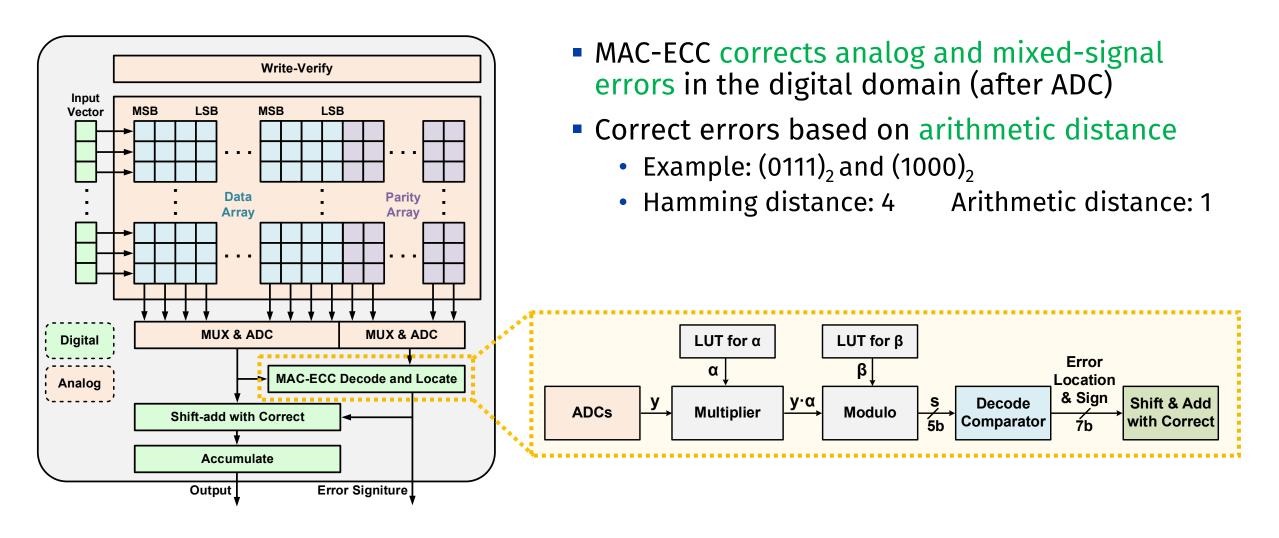
 Supply voltage (VDD) scaling: popular method to toggle systems between different modes of operations



- Scaling VDD from 1.0V to 0.7V reduces ADC sense margin by >50%
  - Reduced sense margin induces more ADC errors



### **MAC-ECC: In-Situ ECC for CIM**



### **Iso-Accuracy Voltage-Scaling**

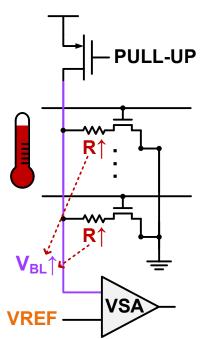
- Voltage scaling allows toggling between high performance and low power modes
- Higher error rates at low VDDs are compensated by allocating more MAC-ECC columns
  - Achieve iso-accuracy voltage scaling (<1% CNN accuracy loss under all tested VDDs)

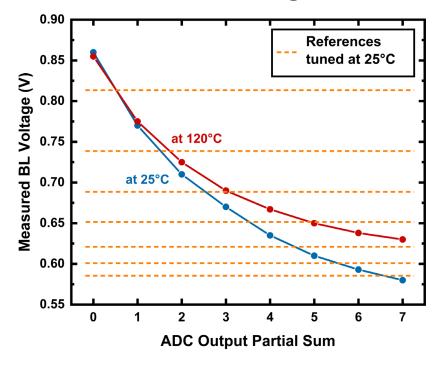
High <b>▲</b>	VDD	Least costly MAC-ECC for <1% loss	Frequency	Energy Efficiency (TOPS/W)	Compute Efficiency (GOPS/mm²)	Energy Overhead	Area Overhead
Performance	1V	No ECC	115MHz	43.0	112.5	0%	0%
	0.9V	(31, 25)	100MHz	46.2	93.1	3.73%	3.1%
	0.8V	(25, 19)	90MHz	52.4	82.8	4.95%	4.11%
Low Power	0.7V	(16, 10)	80MHz	59.1	70.9	7.48%	6.06%

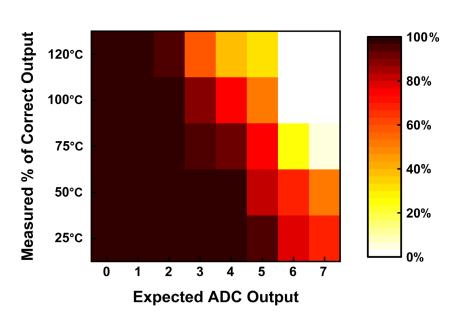


### Challenge: Temperature Fluctuation

- RRAM resistance tends to increase with rising temperature
  - Thus, sensed V<sub>BI</sub> is dependent on temperature
  - Rigid references tuned at one temperature (e.g. 25 °C) works poorly at others (e.g. 120 °C)
  - Mismatch between references and BL voltage curve causes missing ADC codes

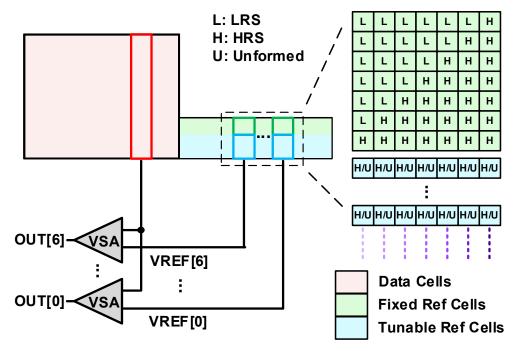






### Temperature-Independent ADC References

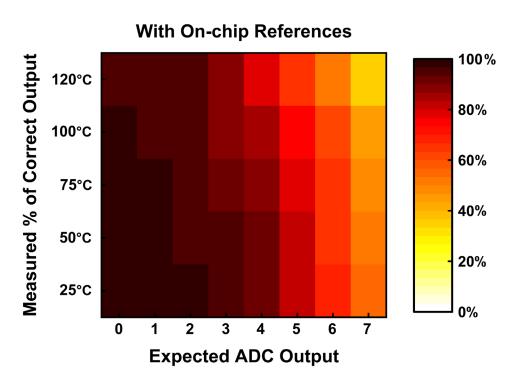
- Use a separate section of RRAM cells for on-chip ADC reference generation
  - RRAM provides self-tracking to temperature
  - Tunability (to different RRAM states) helps cancel ADC offsets
  - Requires ~5% overhead of RRAM cells

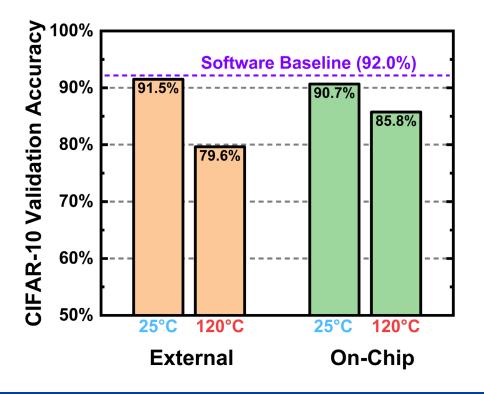




### **Evaluation of ADC References**

- Measured ADC outputs with random test vectors at various temperatures
  - RRAM-based references can retain all ADC codes
  - Network accuracy at 120 °C is recovered by ~6% using temperature-independent references





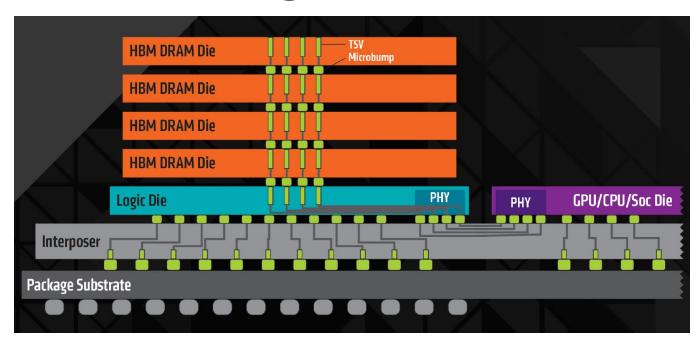


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### Heterogeneous 3-D Integration (H3D)



#### • Advantages:

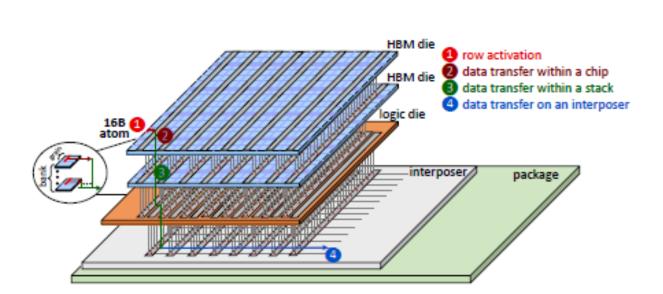
- Compact form factor to store data
- Flexibility to stack different technologies and fabrics into the same package
- State-of-the-art H3D is memory-on-memory (NAND Flash, HBM, 3D V-Cache etc.)

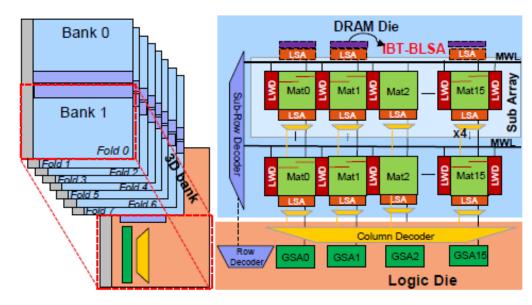


AMD, Gen-1 HBM

### Folded-Banks HBM

- Alternative version of HBM4 optimized for random accesses
  - Redistributes bank subarrays ("folds") across multiple dies and relocates command, control, and global sense amplifiers to an additional base layer

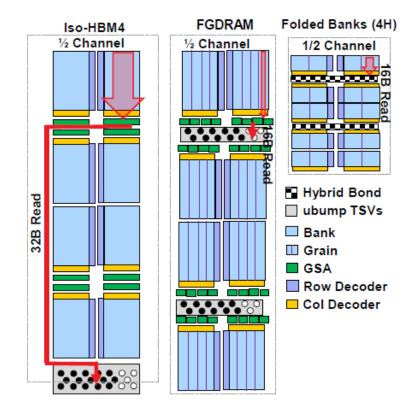






#### Folded-Banks HBM

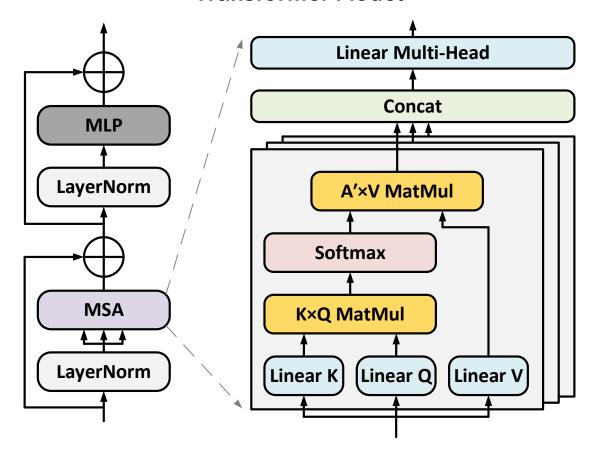
- Novel architecture leads to significant reduction in t<sub>CCD</sub> and t<sub>CL</sub> delays
- Compared to a projected HBM4 design, FB-HBM achieves a 6.7× improvement in random-access performance
- Translates to a 2.28× speedup across HPC and sparse machine learning applications



Parameter	НВМ3	Iso-HBM4	FB-HBM
Technology Node (nm)	16	9	9
Bank Height (µm)	918.4	635.5	95.8
Driver Enable Delay (ns)	0.2	0.2	0.2
CSL Driver Resistance $(\Omega)$	250	300	300
CSL Load Capacitance (fF)	8	8	8
SSA Pre Delay (ns)	0.2	0.2	0.2
Wire Resistance (Ω/mm)	2670	4000	4000
Wire Capacitance (fF/mm)	180	180	180
MDL Driver Resistance $(\Omega)$	200	300	300
TSV Resistance (mΩ/TSV)	_	_	154.9
TSV Capacitance (fF/TSV)	-	_	11.6
CSL Resistance (Ω)	2450	2550	381.8
CSL Capacitance (fF)	173.1	122.7	91.6
MDL Resistance (Ω)	2450	2550	381.8
MDL Capacitance (fF)	165.1	114.7	83.6
t <sub>CCD</sub> (ns)	2.55	2.07	1.044
t <sub>CL</sub> (ns)	15.8	13.4	10.04

### Choice of Memory Technologies for Transformers

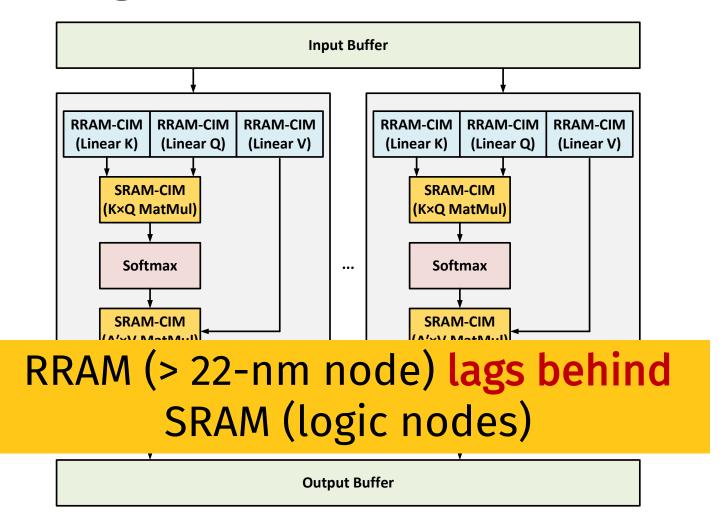
# Multi-head Self-Attention (MSA) in Transformer Model



- MSA is the critical module in transformers
  - Matrix multiplication workloads in MSA involve different properties
- Linear (fully-connected) layer
  - Trained model parameters
  - RRAM: Non-volatility, compact cell size
- Intermediate matrix multiplication (MatMul)
  - Both inputs generated at run-time
  - SRAM: Low access energy, high endurance

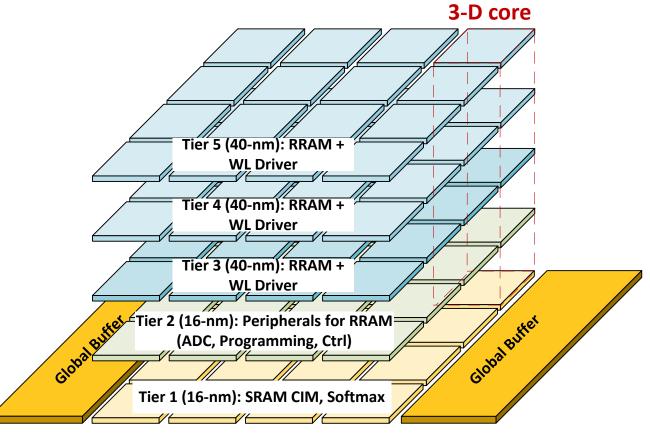


### **Accelerator Design for Transformers**



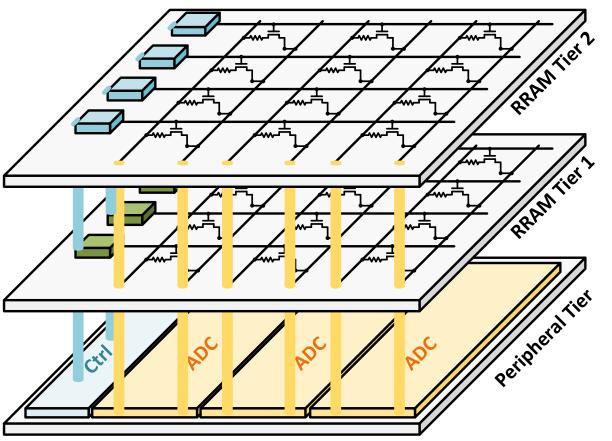


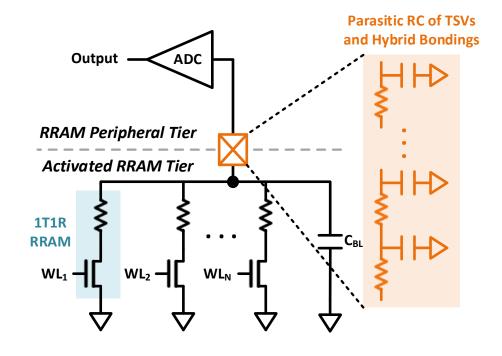
### **H3D Hybrid-CIM Accelerator**



- 3-D tier partitioning
  - RRAM: 3 tiers to increase stack capacity
  - ADC & Digital: 16-nm for lower power and area
- 1.6× improvement in energy efficiency compared to 2-D design (all in 40-nm)

# **Signaling Evaluations**

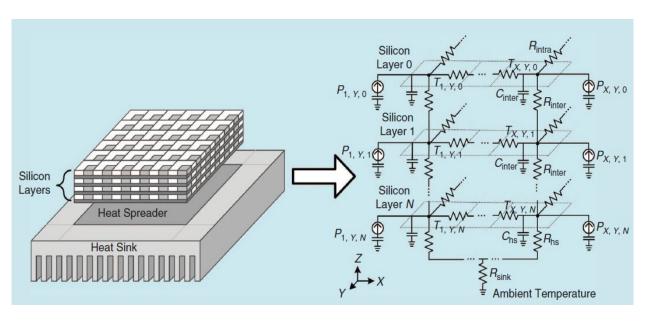




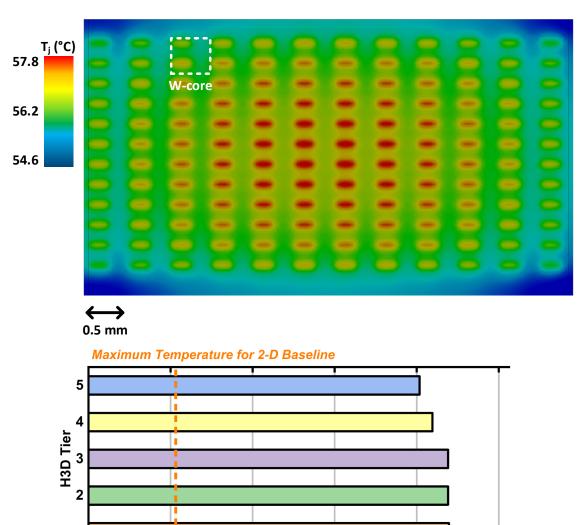
- Parasitic R affects ADC sense margin
  - Tested models experience no accuracy loss
- Parasitic C affects sensing speed
  - 8% reduction in operating frequency



### **Thermal Evaluations**



- 3-D stacking affects heat dissipation
  - Temperature in H3D design is raised by ~15°C compared to 2-D baseline



52

**Maximum Tier Temperature (°C)** 

56

44

60

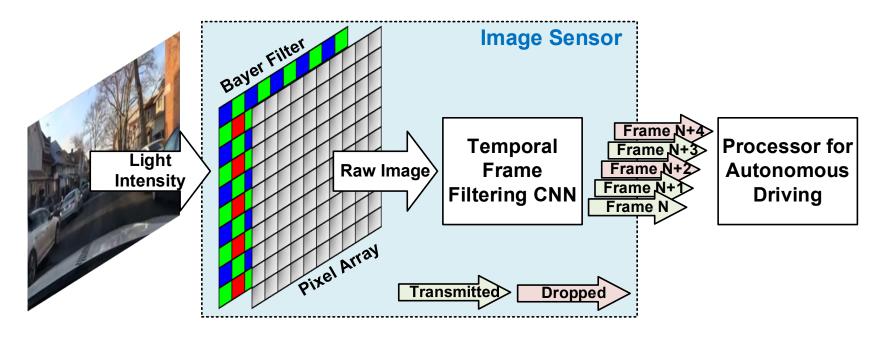
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### Near-Pixel Frame Filtering for Autonomous Driving

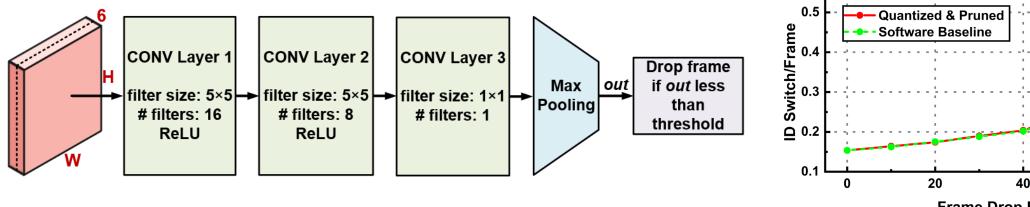
- Near-pixel compute paradigm offers locality benefits
- This work proposes a temporal frame filtering (TFF) network and its near-pixel accelerator, targeting autonomous driving
  - Filter out redundant image frames to reduce system-level data movements

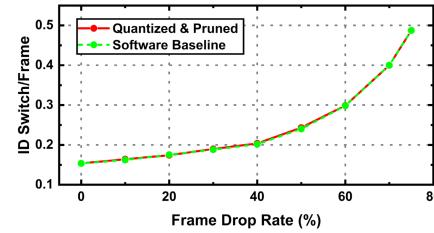




### Temporal Frame Filtering Algorithm

- Temporal Frame Filter (TFF) is a 3-layer CNN
  - Input channel of 6 is from concatenation of current frame and difference frame (both in RGB)
  - Training images are from BDD100K video dataset (1296×720 at 30 FPS)
  - TFF is trained to minimize the ID switch/frame metric that backend Quasi-Dense Tracking (QDTrack) performs on BDD100K





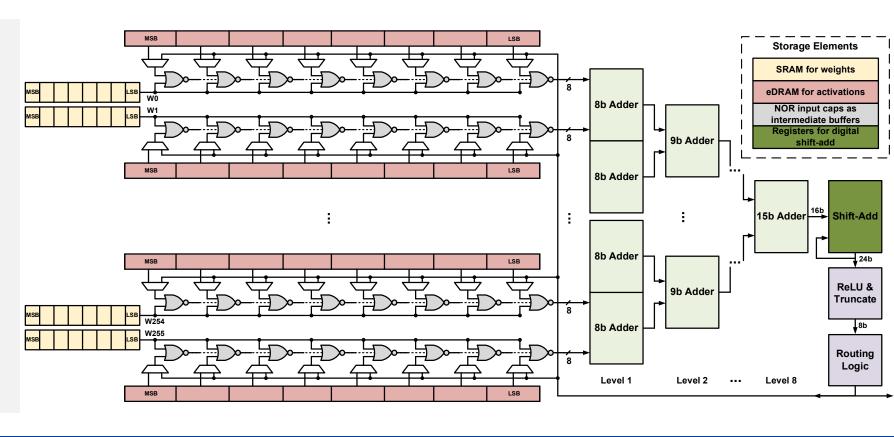


### **Near-Pixel Accelerator with Digital CIM**

- 1MB in-pixel eDRAM-based buffer to retain data for one frame period
- A digital adder tree for complete MAC

380.1 GOPS/mm<sup>2</sup>

Technology	40 nm LP
Activation/weight precisions	8b/8b INT
Area	12.5 mm <sup>2</sup>
Supply voltage	0.9 V
Operating frequency	100 MHz
Power consumption	303.4 mW
Energy efficiency (8×8b MAC)	15.7 TOPS/W

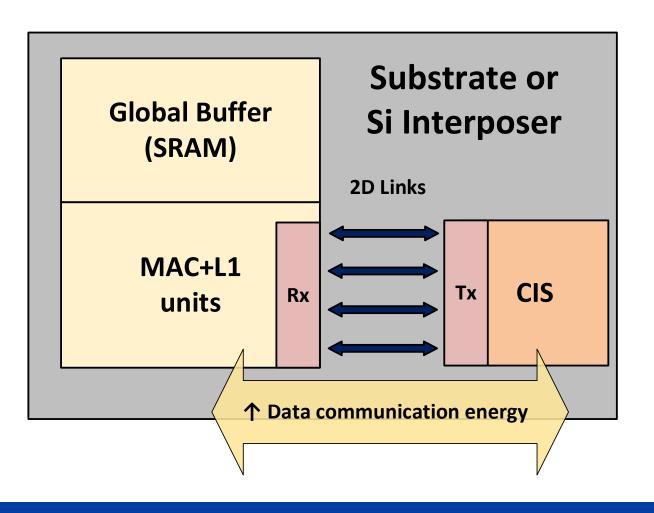


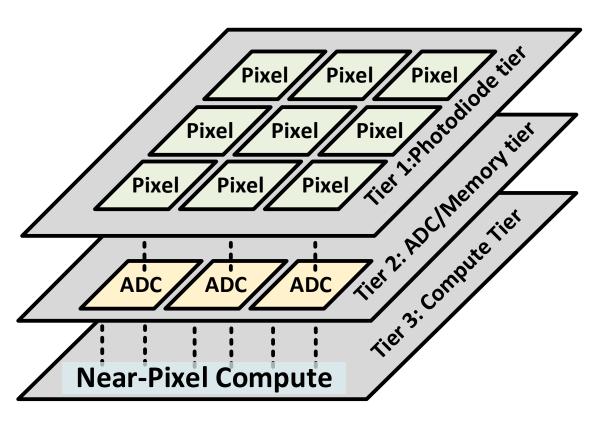


**Compute density** 

 $(8 \times 8b \text{ MAC})$ 

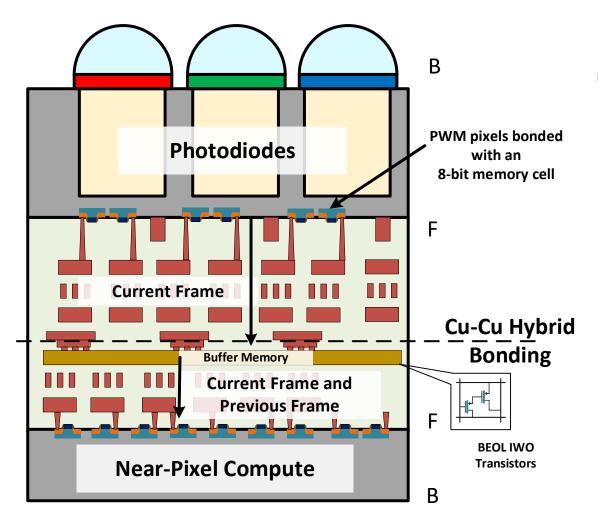
### **Integrating Heterogeneous Components**

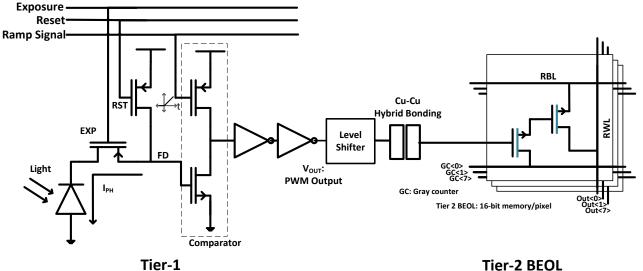






### 3-D Stacked CIS with Near-Pixel Compute





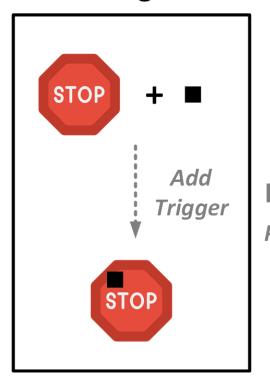
Compared to planar integration design

4× power reduction at the same FPS

# **Procedure of Typical AI Backdoor Attacks**

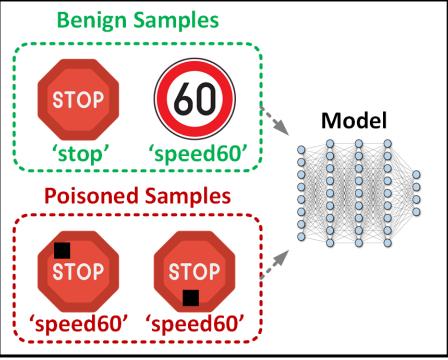
 Backdoor models behave normally with clean inputs, but whenever the trigger is presented, the input will be misclassified

#### **Poisoning Phase**

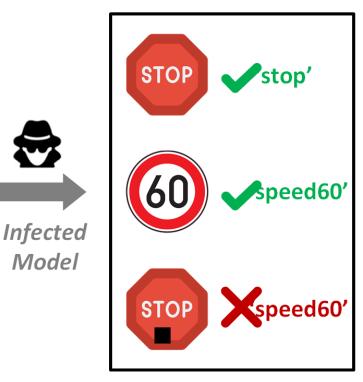




#### **Training Phase**



#### **Inference Phase**



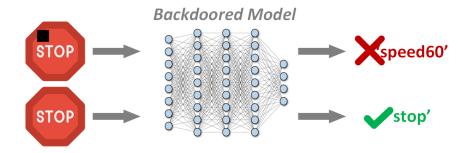
Model



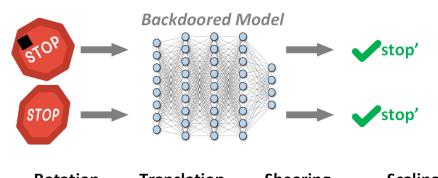
### **Transformation-based Backdoor Defense**

- Exploit the sensitivity of backdoor triggers to spatial or visual alterations
- Enhance model backdoor security without modifying internal model parameters
- Affine transformations
  - linear operations that preserve straight lines and parallelism while modifying their spatial properties
  - distort embedded triggers and compromise their ability to activate the backdoor

#### **Untransformed Images**



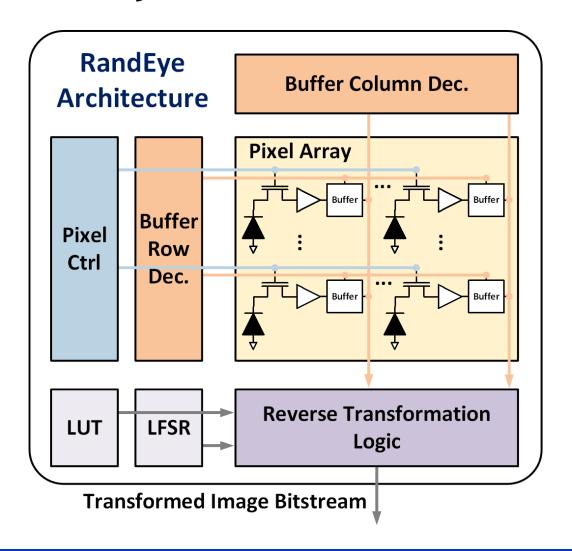
#### **Stochastically Transformed Images**



Kotatio		iransiation				Snearing				Scaling			
$cos(\theta)$ -sin( $\theta$ )	0	1	1	0	TR <sub>x</sub>		1	SH <sub>x</sub>	0		SC <sub>x</sub>	0	0 ]
sin(θ) cos(θ)	0	Ш	0	1	$TR_{y}$		SH <sub>y</sub>	1	0		0	$SC_y$	0
0 0	1		0	0	1		0	0	1		0	0	1



### RandEye Hardware Architecture



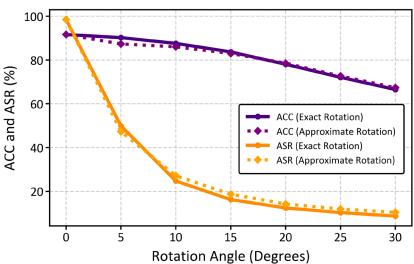
- RandEye supports on-sensor stochastic image transformations for AI backdoor defense
  - Include shear, rotation, and scaling
- RandEye can be integrated with conventional image sensors by adding a few peripheral components
- Potential benefits include independence from AI model's structure, and increased effort required for adversaries to compromise the security measure
- Core modules include on-sensor transformation, pixel decoders, pixel controller, and LFSR
  - Reverse transformation logic that maps each pair of the final pixel coordinates to its original coordinates

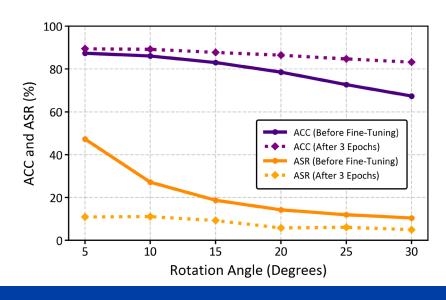


### **Evaluation of Approximate Rotation-based Defense**

 Evaluate the effect of hardware-based onsensor rotations on ACC and ASR compared to the software-based baseline (ResNet-18)

- On-sensor rotations consider both the arithmetic optimizations as well as the reverse transformation
- With hardware-based rotation, ACC only drops by an average of 0.58% across rotation angles
- RandEye can be used with model fine-tuning to further restore ACC and suppress ASR







### **Summary**

#### Theme 1: Emerging Computing Paradigms

- RRAM-based CIM chip tape-out in TSMC 40-nm for efficient AI inference
- PVT-robust circuit design techniques

#### Theme 2: More-than-Moore Heterogenous System

- Folded-Banks HBM for irregular bandwidth applications
- Heterogeneous 3D hybrid-CIM accelerator for vision transformer

#### Theme 3: Algorithm/Hardware Co-Design

- Near-pixel frame filtering with CIS & processing co-integration
- On-sensor stochastic image transformation for backdoor trigger deactivation

